Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt®



- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		1200	V			
Average rectified forward current	I _{F(AV)}	T _{Sp} = 144 °C, D = 0.5	1	~			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 8.3 ms sine pulse	21	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C			



SMA (DO-214AC)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	1 A			
V _R	1200 V			
V _F at I _F	1.10 V			
t _{rr}	75 ns			
T _J max.	175 °C			
Package	SMA (DO-214AC)			
Circuit configuration	Single			

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	1200	-	-	
	V _F	I _F = 1 A	-	1.35	1.80	v
Forward voltage, per diode		V _F	I _F = 1 A, T _J = 125 °C	-	1.17	1.55
		I _F = 1 A, T _J = 150 °C	-	1.10	1.44	
Reverse leakage current, per diode	I_	$V_{R} = V_{R}$ rated	-	-	5	μA
nevelse leakage current, per diode	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	50	μΑ
Junction capacitance	CT	V _R = 1200 V	-	3.5	-	pF

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		$I_{\rm F} = 0.5 \text{ A}, I_{\rm R} = 1 \text{ A}$	A, I _{rr} = 0.25 A	-	-	75		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	99	-	ns	
		T _J = 125 °C		-	137	-		
Pools recovery ourrent	1	T _J = 25 °C	I _F = 1 A, dI _F /dt = 200 A/μs,	-	3.5	-	А	
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 800 \text{ V}$	-	4.5	-	A	
	0	T _J = 25 °C		-	150	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	286	-	no	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	15	18	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with recommended pad size	-	110	-	°C/W	
Approximate weight				0.07		g	
Marking device		Case style SMA (DO-214AC)		11	112		

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

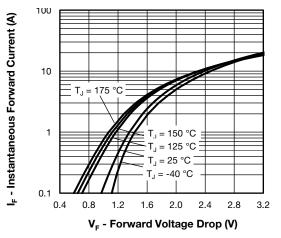


Fig. 1 - Typical Forward Voltage Drop Characteristics

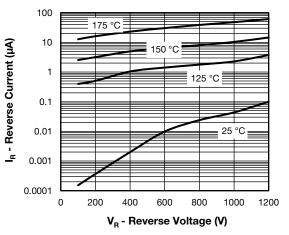


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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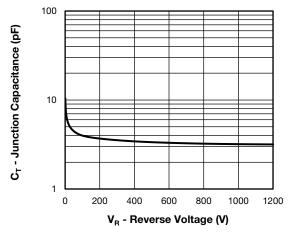
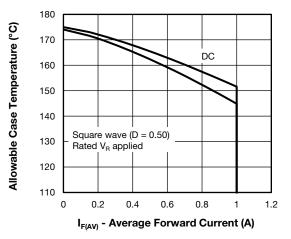
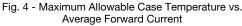


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





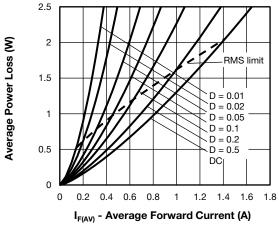


Fig. 5 - Forward Power Loss Characteristics

 $^{(1)} \mbox{ Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \mbox{ forward power loss } = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 5);$

 Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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VS-E7MH0112HM3

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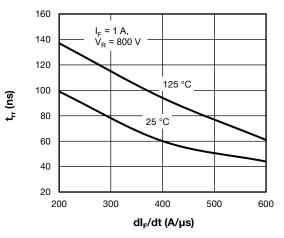
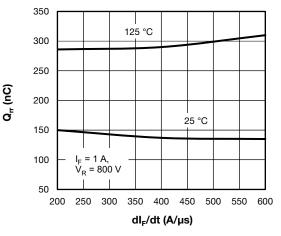


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt





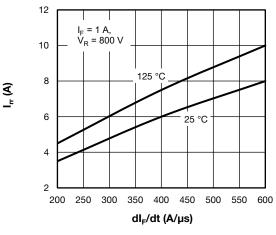


Fig. 8 - Irr (A) vs. dI_F/dt

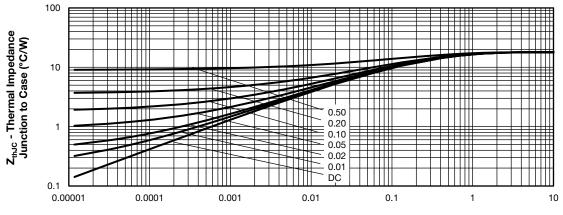
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Note

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t₁ - Rectangular Pulse Duration (s)

Fig. 9 - Transient Thermal Impedance, Junction to Case

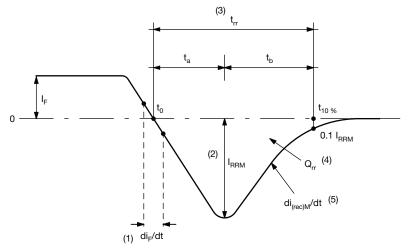


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

⁽¹⁾ di_F/dt - rate of change of current through zero crossing

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- $^{(2)}\ \ I_{RRM}$ peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~Q_{rr}$ area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_r} I(t)dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

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ORDERING INFORMATION TABLE

Device code	vs-	E	7	м	н	01	12	н	М3
		2	3	4	5	6	7	8	9
	1	- Visl	nay Sen	niconduo	ctors pro	oduct			
	2		cuit conf single c	iguratior liode	n:				
	3.		•	jeneratio	on 7				
	4	- M =	SMA p	ackage					
	5		cess typ hyperfa	e, ist recov	/ery				
	6	- Cur	rent rati	ng (01 =	= 1 A)				
	7.	- Volt	tage coo	de (12 =	1200 V)			
	8	. Н=	AEC-Q	101 qua	lified				
	9	- M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	tions lea

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-E7MH0112HM3/I	7500	7500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95400				
Part marking information	www.vishay.com/doc?95472				
Packaging information	www.vishay.com/doc?95404				



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